
Oral presentation | 15. Crystal Engineering | 15.4 III-V-group nitride crystals

[19p-B5-1~22]15.4 III-V-group nitride crystals

Thu. Sep 19, 2013 1:00 PM - 7:15 PM B5 (TC2 2F-201)

△ : Young Scientist Oral Presentation Award Applied

▲ : English Presentation

▼ : Both Award Applied and English Presentation

1:00 PM - 1:30 PM

[19p-B5-1][JSAP Paper Award Speech](30 min.) Preparation of a Freestanding AlN Substrate from a Thick AlN Layer Grown by Hydride Vapor Phase Epitaxy on a Bulk AlN Substrate Prepared by Physical Vapor Transport

○Yoshinao Kumagai¹, Yuki Kubota², Toru Nagashima^{1,2}, Toru Kinoshita², Rafael Dalmau³, Raoul Schlessler³,
Baxter Moody³, Jinqiao Xie³, Hisashi Murakami¹, Akinori Koukitu¹, Zlatko Sitar^{3,4} (TUAT¹, TOKUYAMA²,
HexaTech³, NC State Univ.⁴)